

MAPC-A3025

Rev.V1

Features

- Unmatched, Ideal for Pulsed Operation
- Suitable for Linear & Saturated Applications
- CW & Pulsed Operation: 60 W Output Power
- 28 V Operation

Applications

2-Way Private Radio, Broadband Amplifiers, Cellular Infrastructure, Test Instrumentation, Class A, AB, Linear amplifiers suitable for OFDM, W-CDMA, EDGE, CDMA waveforms

Description

The MAPC-A3025 is a high power GaN on Silicon Carbide HEMT D-mode amplifier. The device is suitable for pulsed operation with output power levels of 60W (47.8 dBm) in a DFN Package.

Typical Performance:

Measured Evaluation Test Fixture at P_{IN} = 34 dBm, 100 µs pulse width, 10% duty cycle,

V_{DS} = 28 V, I_{DQ} = 400 mA, T_C = 25°C

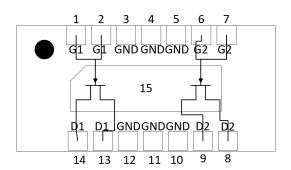
Frequency (GHz)	Output Power (dBm)	Gain (dB)	η _D (%)
2.60	47.8	13.8	77.0
2.65	47.5	13.7	77.0
2.70	47.2	13.3	76.0

Ordering Information

Part Number	Package
MAPC-A3025-ABPPR	Bulk Quantity
MAPC-A3025-SBPPR	Sample Board



Functional Schematic



Pin Configuration¹

Pin#	Pin Name	Function			
1,2	G1	RF Input / Gate 1			
13,14	D1	RF Output / Drain 1			
6,7	G2	RF Input / Gate 2			
8,9	D2	RF Output / Drain 2			
3,4,5,10,11, 12,15	NC	Ground / Source			

The exposed pad centered on the package bottom must be connected to RF and DC ground.

^{*} Restrictions on Hazardous Substances, compliant to current RoHS EU directive.



MAPC-A3025

Rev.V1

RF Electrical Characteristics: $T_C = 25^{\circ}C$, $V_{DS} = 28 \text{ V}$, $I_{DQ} = 400 \text{ mA}$ Note: Performance in MACOM Evaluation Test Fixture, 50Ω system

Parameter	Test Conditions	Symbol	Min.	Тур.	Max.	Units
Power Gain	Pulsed ² , 2.6 GHz, P _{IN} = 34 dBm	G _{SAT}	_	13.8		dB
Saturated Drain Efficiency	Pulsed ² , 2.6 GHz, P _{IN} = 34 dBm	η_{SAT}	_	77.0		%
Saturated Output Power	Pulsed ² , 2.6 GHz, P _{IN} = 34 dBm	P _{SAT}	_	47.8	_	dBm
Ruggedness: Output Mismatch	All phase angles	Ψ	VSV	VR = 10:	1; No Da	ımage

RF Electrical Specifications: $T_A = 25^{\circ}C$, $V_{DS} = 28 \text{ V}$, $I_{DQ} = 400 \text{ mA}$ Note: Performance in MACOM Production Test Fixture, 50 Ω system

Parameter	Test Conditions 5		Min.	Тур.	Max.	Units
Power Gain	Pulsed ² , 2.6 GHz, P _{IN} = 34 dBm	G _{SAT}	13.4	13.7		dB
Saturated Drain Efficiency	Pulsed ² , 2.6 GHz, P _{IN} = 34 dBm	η _{SAT}	65	74	_	%
Saturated Output Power	Pulsed ² , 2.6 GHz, P _{IN} = 34 dBm	P _{SAT}	47.4	47.7	_	dBm

^{2.} Pulse details: 100 µs pulse width, 10% Duty Cycle.

DC Electrical Characteristics T_A = 25°C

Parameter	Test Conditions S		Min.	Тур.	Max.	Units
Drain-Source Leakage Current	$V_{GS} = -8 \text{ V}, V_{DS} = 10 \text{ V}$	I _{DLK}	-	-	2	mA
Gate-Source Leakage Current	V _{GS} = -8 V, V _{DS} = 10 V	I _{GLK}	-2	-	-	mA
Gate Threshold Voltage	$V_{DS} = 28 \text{ V}, I_{D} = 14.4 \text{ mA}$	V _T	-3.6	-3.1	-2.4	V
Gate Quiescent Voltage	V_{DS} = 28 V, I_{D} = 300 mA	V_{GSQ}	-	-2.4	-	V



MAPC-A3025

Rev.V1

Absolute Maximum Ratings 3,4,5,6

Parameter	Absolute Maximum		
Drain Source Voltage, V _{DS}	28 V		
Gate Source Voltage, V _{GS}	-10 to 2 V		
Gate Current, I _G	14 mA		
Storage Temperature Range	-65°C to +150°C		
Case Operating Temperature Range	-40°C to +85°C		
Channel Operating Temperature Range, T _{CH}	-40°C to +225°C		

^{3.} Exceeding any one or combination of these limits may cause permanent damage to this device.

Thermal Characteristics

Parameter	Test Conditions	Symbol	Typical	Units
Thermal Resistance using Finite Element Analysis	V_{DS} = 28 V, P_{DISS} = 43.2 W T_{C} = 85°C, T_{CH} = 225°C	$R_{\theta}(FEA)$	1.83	°C/W
Thermal Resistance using Finite Element Analysis (per side)	$V_{DS} = 28 \text{ V}, P_{DISS} = 21.6 \text{ W}$ $T_{C} = 85^{\circ}\text{C}, T_{CH} = 225^{\circ}\text{C}$	$R_{\theta}(FEA)$	3.65	°C/W

Handling Procedures

Please observe the following precautions to avoid damage:

Static Sensitivity

Gallium Nitride Circuits are sensitive to electrostatic discharge (ESD) and can be damaged by static electricity. Proper ESD control techniques should be used when handling these devices.

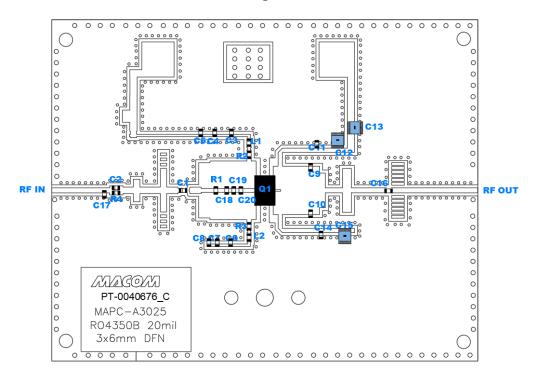
^{4.} MACOM does not recommend sustained operation above maximum operating conditions.

^{5.} Operating at drain source voltage V_{DS} < 28 V will ensure MTTF > 2 x 10⁶ hours. 6. Operating at nominal conditions with $T_{CH} \le 225^{\circ}$ C will ensure MTTF > 2 x 10⁶ hours.



MAPC-A3025 Rev.V1

Evaluation Board and Recommended Tuning Solution 2.6 - 2.7GHz



Reference Designator	Value	Tolerance	Manufacturer	Part Number
C1	27 pF	±5%	Johanson	QSCT251Q270J1GV001E
R1	100 Ω	±5%	Vishay	CRCW12100000Z0EAHP
R2,R3	10 Ω	±1%	Yageo	RC0603FR-0710KL
C2	2.4 pF	±0.1pF	Johanson	QSCT251Q2R4B1GV001E
R4	150 Ω	±5%	Yageo	RC0603JR-13150RL
L1, L2	22 nH	±5%	Coilcraft	0201HL-22NXJRW
C3, C6	27 pF	±5%	Johanson	QSCT251Q270J1GV001E
C7, C4, C12, C15	1000 pF	±10%	Murata	GRM21AR72E102KW01D
C5, C8, C13, C16	2.2 µF	±20%	Murata	GRM21BD72A225ME01K
C9, C10	0.6 pF	±0.05pF	Johanson	QSCT251Q0R6A1GV001E
C11, C14	20 pF	±5%	Johanson	QSCT251Q200J1GV001E
C17	15 pF	±5%	Johanson	QSCT251Q150J1GV001E
C18, C19, C20	1 pF	±0.1pF	Johanson	QSCT251Q1R0B1GV001E

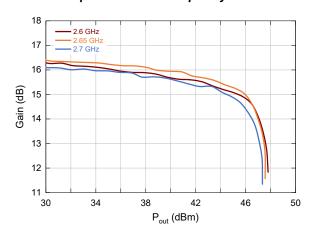


MAPC-A3025

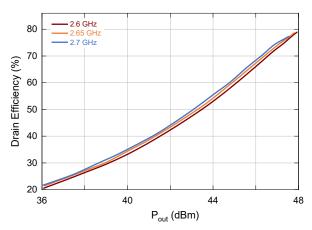
Rev.V1

Typical Performance Curves as Measured in the 2.6 - 2.7 GHz Evaluation Board: Pulsed 2 , V_{DS} = 28 V, I_{DQ} = 400 mA, T_C = 25 $^{\circ}$ C (Unless Otherwise Noted)

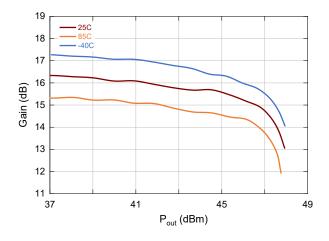
Gain vs. Output Power and Frequency



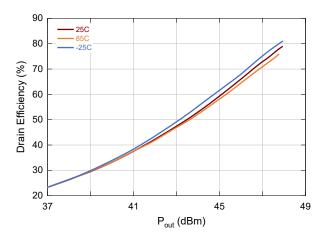
Drain Efficiency vs. Output Power and Frequency



Gain vs. Output Power and Tc. 2.6 GHz



Drain Efficiency vs. Output Power and Tc, 2.6 GHz



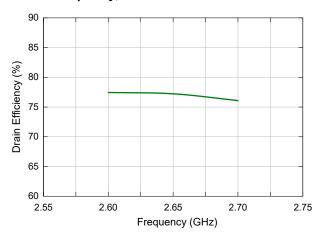


MAPC-A3025

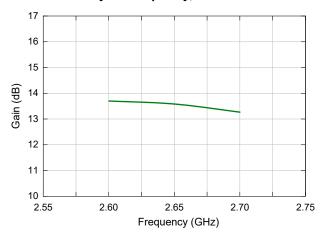
Rev.V1

Typical Performance Curves as Measured in the 2.6 - 2.7 GHz Evaluation Board: Pulsed 2 , 2.6 GHz, V_{DS} = 28 V, I_{DQ} = 400 mA, T_C = 25 $^{\circ}$ C (Unless Otherwise Noted)

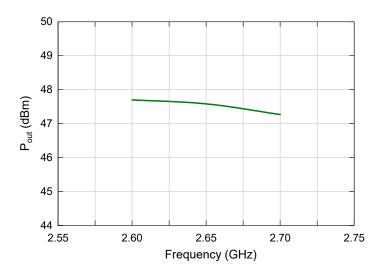
Gain vs. Frequency, Fixed P_{IN} = 34 dBm



Drain Efficiency vs. Frequency, Fixed P_{IN} = 34 dBm



Output Power vs. Frequency, Fixed $P_{IN} = 34 \text{ dBm}$

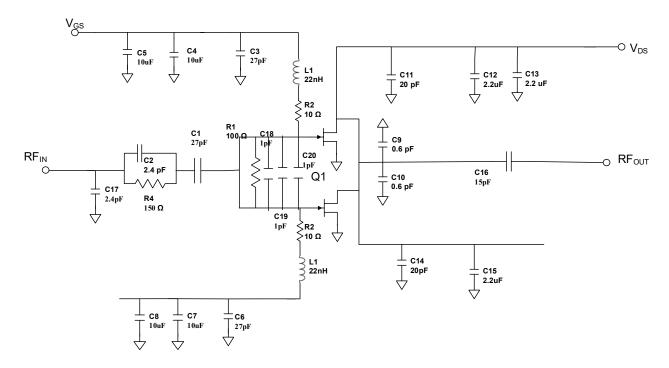




MAPC-A3025

Rev.V1

Evaluation Test Fixture and Recommended Tuning Solution 2.6 - 2.7 GHz



Description

Parts measured on evaluation board (20 mil thick RO4350B). Matching is provided using a combination of lumped elements and transmission lines as shown in the simplified schematic above. Recommended tuning solution component placement, transmission lines, and details are shown on the next page.

Bias Sequencing Turning the device ON

- 1. Set V_{GS} to pinch-off (V_P).
- 2. Turn on V_{DS} to nominal voltage (50 V).
- 3. Increase V_{GS} until I_{DS} current is reached.
- 4. Apply RF power to desired level.

Turning the device OFF

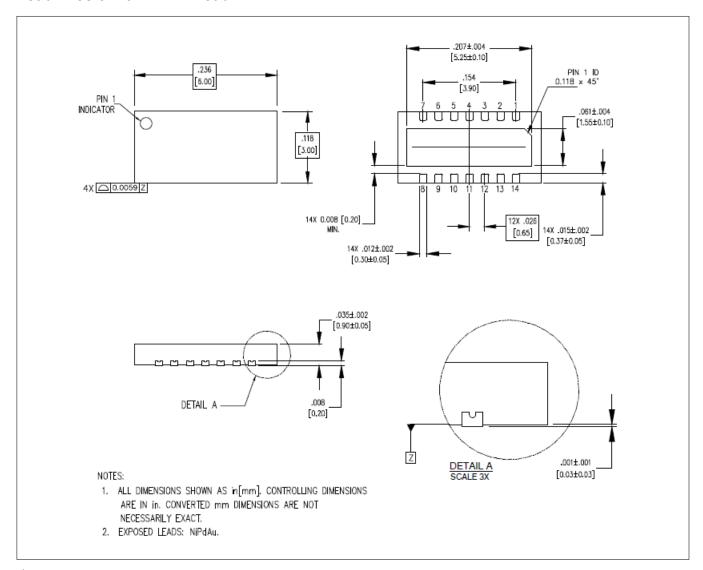
- 1. Turn the RF power OFF.
- 2. Decrease V_{GS} down to V_P pinch-off.
- 3. Decrease V_{DS} down to 0 V.
- 4. Turn off V_{GS}.



MAPC-A3025

Rev.V1

Lead-Free 3 x 6 mm 14-Lead DFN[†]



[†] Reference Application Note S2083 for lead-free solder reflow recommendations. Meets JEDEC moisture sensitivity level 1 requirements . Plating is Ni/Pd/Au.

GaN Amplifier 28 V, 60 W DC - 6 GHz



MACOM PURE CARBIDE.

MAPC-A3025

Rev.V

MACOM Technology Solutions Inc. ("MACOM"). All rights reserved.

These materials are provided in connection with MACOM's products as a service to its customers and may be used for informational purposes only. Except as provided in its Terms and Conditions of Sale or any separate agreement, MACOM assumes no liability or responsibility whatsoever, including for (i) errors or omissions in these materials; (ii) failure to update these materials; or (iii) conflicts or incompatibilities arising from future changes to specifications and product descriptions, which MACOM may make at any time, without notice. These materials grant no license, express or implied, to any intellectual property rights.

THESE MATERIALS ARE PROVIDED "AS IS" WITH NO WARRANTY OR LIABILITY, EXPRESS OR IMPLIED, RELATING TO SALE AND/OR USE OF MACOM PRODUCTS INCLUDING FITNESS FOR A PARTICULAR PURPOSE, MERCHANTABILITY, INFRINGEMENT OF INTELLECTUAL PROPERTY RIGHT, ACCURACY OR COMPLETENESS, OR SPECIAL, INDIRECT, INCIDENTAL, OR CONSEQUENTIAL DAMAGES WHICH MAY RESULT FROM USE OF THESE MATERIALS.

MACOM products are not intended for use in medical, lifesaving or life sustaining applications. MACOM customers using or selling MACOM products for use in such applications do so at their own risk and agree to fully indemnify MACOM for any damages resulting from such improper use or sale.